

# ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

Stylesheet Version v18.0

Title of Invention	METHOD OF FORMING A LOW VOLTAGE GATE OXIDE LAYER AND TUNNEL OXIDE LAYER IN AN EEPROM CELL						
Application Number :	10/717149						
Confirmation Number:	6780						
First Named Applicant:	Alan Renninger						
Attorney Docket Number:	ATM-262						
Art Unit:	2818						
Examiner:							
Search string:	( 5882993 or 5254489 ).pn						
<p><u>Certification:</u> This Information Disclosure Statement was submitted under the following conditions, which satisfies the requirement under 37 CFR 1.97(e). The filer certified:</p> <p>That each item of information contained in the information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the information disclosure statement.</p>							
<h3>US Patent Documents</h3>							
<p>Note: Applicant is not required to submit a paper copy of cited US Patent Documents</p>							
init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
	1	5882993	1999-03-16	Gardner et al.	A1	438	591
	2	5254489	1993-10-19	Nakata	A1	437	40
<h3>Signature</h3>							
Examiner Name 				Date 			